

A METHOD AND STRUCTURE FOR IMPROVED ALIGNMENT TOLERANCE  
IN MULTIPLE, SINGULARIZED PLUGS

Abstract of the Disclosure

5           An improved method and structure which increases the alignment tolerances  
in multiple, singularized plugs are provided. The invention discloses a novel  
method for forming individual plug contacts with increased surface area for  
improved registration between semiconducting layers. Also the improved plug  
contacts are particularly well suited to receiving contact formations which have any  
10 taper to them. IGFETS and other devices formed from this design can be used in a  
variety of beneficial applications, e.g. logic or memory.

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